



Pb Free Plating Product

2SC2625

80 WATT NPN EPITAXIAL SILICON TRANSISTOR

■ Features

- High voltage, High speed switching
- High reliability

■ Applications

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

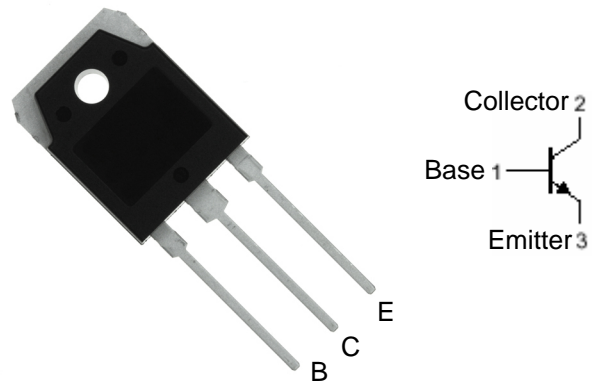


Fig.1 simplified outline (TO-3PB) and symbol

■ Maximum ratings and characteristics

● Absolute maximum ratings (T_c=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Collector-Base voltage	V _{CB0}	450	V
Collector-Emitter voltage	V _{CEO}	400	V
Collector-Emitter voltage	V _{CEO(SUS)}	400	V
Emitter-Base voltage	V _{EBO}	7	V
Collector current	I _C	10	A
Base current	I _B	3	A
Collector power dissipation	P _C	80	W
Operating junction temperature	T _j	+150	°C
Storage temperature	T _{stg}	-55 to +150	°C

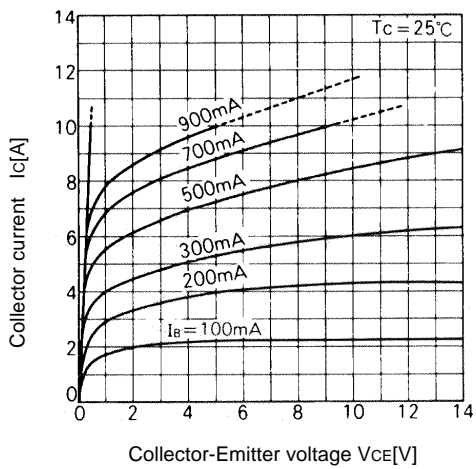
● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Base voltage	V _{CB0}	I _{CBO} = 1mA	450			V
Collector-Emitter voltage	V _{CEO}	I _{CEO} = 10mA	400			V
Collector-Emitter voltage	V _{CEO(SUS)}	I _C = 1A	400	-		V
Emitter-Base voltage	V _{EBO}	I _{EBO} = 0.1mA	7	-		V
Collector-Base leakage current	I _{CBO}	V _{CB0} = 450V		-	1.0	mA
Emitter-Base leakage current	I _{EBO}	V _{EBO} = 7V		-	0.1	mA
D.C. current gain	h _{FE}	I _C = 4A, V _{CE} = 5V	10			
Collector-Emitter saturation voltage	V _{CE(Sat)}	I _C = 4A, I _B = 0.8A			1.2	V
Base-Emitter saturation voltage	V _{BE(Sat)}				1.5	V
*1	t _{on}	I _C = 7.5A, I _{B1} = -I _{B2} = 1.5A			1.0	μs
Switching time	t _{stg}	R _L = 20 ohm, P _w = 20μs Duty=<2%			2.0	μs
	t _f				1.0	μs

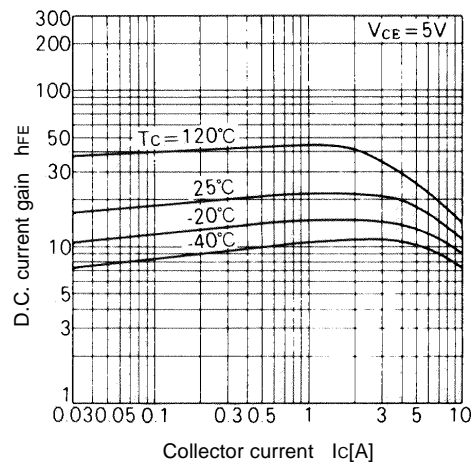
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(j-c)}	Junction to case			1.55	°C/W

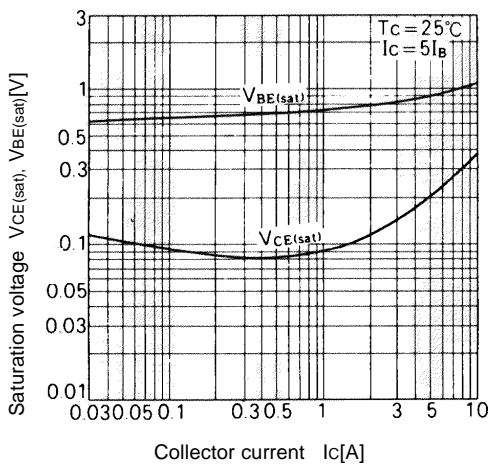
Characteristics



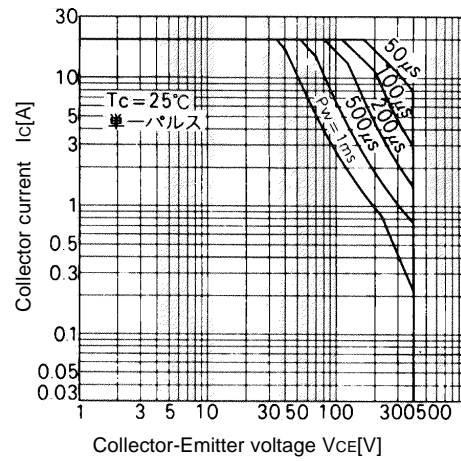
Collector Output Characteristics



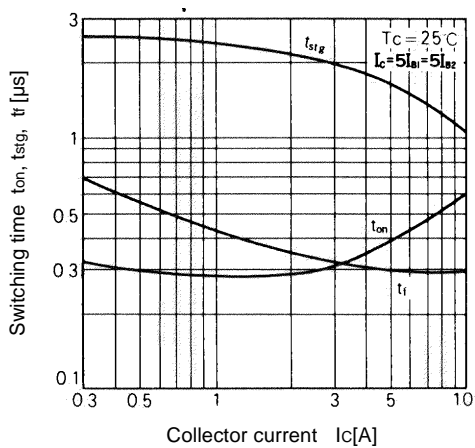
DC Current Gain



Base and Collector Saturation Voltage



Safe Operating Area



Switching Time

*1 Switching Time Test Circuit

